

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1. (Previously Presented) A method for removing a resist pattern, comprising:
forming a metal film over a substrate;
forming a resist pattern of a positive resist composition containing a photosensitizer over the metal film;
etching the metal film by using the resist pattern;
irradiating the resist pattern with a light having a photosensitive wavelength region of the photosensitizer after etching the metal film; and
removing the resist pattern by using a resist stripper.
2. (Previously Presented) A method for removing a resist pattern, comprising:
forming a metal film over a substrate;
forming a resist pattern of a positive resist composition containing a photosensitizer over the metal film;
etching the metal film by using the resist pattern;
removing the resist pattern by using a resist stripper;
irradiating an unprocessed portion of the resist pattern with a light having a photosensitive wavelength region of the photosensitizer after removing the resist pattern; and
treating the unprocessed portion of the resist pattern by using a developer.
3. (Previously Presented) A method for manufacturing a semiconductor device, comprising:
forming a metal film over a substrate;

forming a resist pattern of a positive resist composition containing a photosensitizer over the metal film;

etching the metal film by using the resist pattern;

irradiating the resist pattern with a light having a photosensitive wavelength region of the photosensitizer after etching the metal film; and

performing a resist removing process on the resist pattern.

4. (Previously Presented) A method for manufacturing a semiconductor device, comprising:

forming a metal film over a substrate;

forming a resist pattern of a positive resist composition containing a photosensitizer over the metal film;

etching the metal film by using the resist pattern;

removing the resist pattern by using a resist stripper;

irradiating an unprocessed portion of the resist pattern with a light having a photosensitive wavelength region of the photosensitizer after removing the resist pattern; and

treating the unprocessed portion of the resist pattern by using a developer after irradiating the resist pattern with the light having the photosensitive wavelength region of the photosensitizer.

5. (Previously Presented) A method for removing a resist pattern according to claim 1, wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type, and

wherein the photosensitizer is diazonaphthoquinone (DNQ).

6. (Previously Presented) A method for removing a resist pattern according to claim 2, wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type, and

wherein the photosensitizer is diazonaphthoquinone (DNQ).

7. (Previously Presented) A method for manufacturing a semiconductor device according to claim 3,

wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type, and

wherein the photosensitizer is diazonaphthoquinone (DNQ).

8. (Previously Presented) A method for manufacturing a semiconductor device according to claim 4,

wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type, and

wherein the photosensitizer is diazonaphthoquinone (DNQ).

9. (Previously Presented) A method for removing a resist pattern according to claim 2, wherein the metal film forms an electrode of a thin film transistor.

10. (Previously Presented) A method for manufacturing a semiconductor device according to claim 3,

wherein the metal film forms an electrode of a thin film transistor.

11. (Previously Presented) A method for manufacturing a semiconductor device according to claim 4,

wherein the metal film forms an electrode of a thin film transistor.

12-16. (Canceled)

17. (Previously Presented) A method for manufacturing a semiconductor device according to claim 3, wherein a range of an exposure period of time to irradiate the resist pattern with the light having the photosensitive wavelength region of the photosensitizer is from 1 seconds to 30 seconds.

18. (Previously Presented) A method for manufacturing a semiconductor device according to claim 4, wherein a range of an exposure period of time to irradiate the resist pattern with the light having the photosensitive wavelength region of the photosensitizer is from 1 seconds to 30 seconds.

19. (Canceled)

20. (New) A method for removing a resist pattern according to claim 1, wherein the substrate is selected from the group consisting of a glass, a quartz, a semiconductor, a plastic, a plastic film, a metal, a glass-epoxy resin, and a ceramic.

21. (New) A method for removing a resist pattern according to claim 2, wherein the substrate is selected from the group consisting of a glass, a quartz, a semiconductor, a plastic, a plastic film, a metal, a glass-epoxy resin, and a ceramic.

22. (New) A method for manufacturing a semiconductor device according to claim 3, wherein the substrate is selected from the group consisting of a glass, a quartz, a semiconductor, a plastic, a plastic film, a metal, a glass-epoxy resin, and a ceramic.

23. (New) A method for manufacturing a semiconductor device according to claim 4, wherein the substrate is selected from the group consisting of a glass, a quartz, a semiconductor, a plastic, a plastic film, a metal, a glass-epoxy resin, and a ceramic.

24. (New) A method for removing a resist pattern according to claim 1, wherein the metal film comprises a material selected from the group consisting of aluminum, titanium, molybdenum, tantalum, and tungsten.

25. (New) A method for removing a resist pattern according to claim 2, wherein the metal film comprises a material selected from the group consisting of aluminum, titanium, molybdenum, tantalum, and tungsten.

26. (New) A method for manufacturing a semiconductor device according to claim 3, wherein the metal film comprises a material selected from the group consisting of aluminum, titanium, molybdenum, tantalum, and tungsten.

27. (New) A method for manufacturing a semiconductor device according to claim 4, wherein the metal film comprises a material selected from the group consisting of aluminum, titanium, molybdenum, tantalum, and tungsten.